



element14

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[AD7512DIJNZ](#)

[AD7511DIKNZ](#)

[AD7510DIJNZ](#)

[AD7512DIKNZ](#)

EN

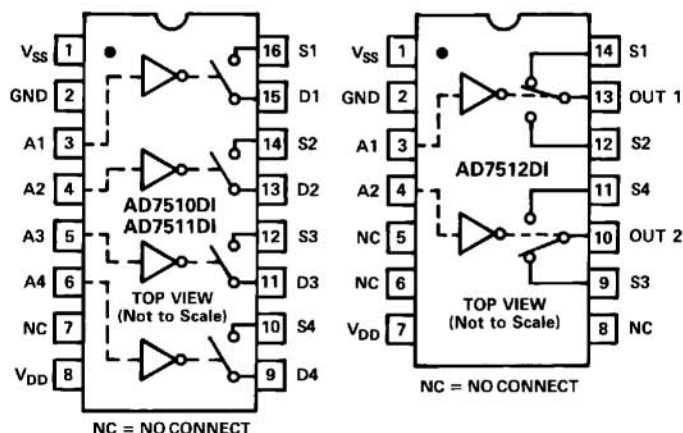
This Datasheet is presented by
the manufacturer

DE

Dieses Datenblatt wird vom
Hersteller bereitgestellt

FR

Cette fiche technique est
présentée par le fabricant

AD7510DI/AD7511DI/AD7512DI
FEATURES
Latch-Proof
Overvoltage-Proof: $\pm 25V$
Low R_{ON} : 75Ω
Low Dissipation: 3mW
TTL/CMOS Direct Interface
Silicon-Nitride Passivated
Monolithic Dielectrically-Isolated CMOS
Standard 14-/16-Pin DIPs and
20-Terminal Surface Mount Packages
DIP FUNCTIONAL DIAGRAMS

GENERAL DESCRIPTION

The AD7510DI, AD7511DI and AD7512DI are a family of latch proof dielectrically isolated CMOS switches featuring overvoltage protection up to $\pm 25V$ above the power supplies. These benefits are obtained without sacrificing the low "ON" resistance (75Ω) or low leakage current ($500pA$), the main features of an analog switch.

The AD7510DI and AD7511DI consist of four independent SPST analog switches packaged in either a 16-pin DIP or a 20-terminal surface mount package. They differ only in that the digital control logic is inverted. The AD7512DI has two independent SPDT switches packaged either in a 14-pin DIP or a 20-terminal surface mount package.

Very low power dissipation, overvoltage protection and TTL/CMOS direct interfacing are achieved by combining a unique circuit design and a dielectrically isolated CMOS process. Silicon nitride passivation ensures long term stability while monolithic construction provides reliability.

CONTROL LOGIC

AD7510DI: Switch "ON" for Address "HIGH"

AD7511DI: Switch "ON" for Address "LOW"

AD7512DI: Address "HIGH" makes S1 to Out 1 and S3 to Out 2

ORDERING GUIDE

Model ¹	Temperature Range	Package Option ²
AD7510DIKN	0 to +70°C	N-16
AD7510DIKP	0 to +70°C	P-20A
AD7510DIKQ	-25°C to +85°C	Q-16
AD7510DISQ	-55°C to +125°C	Q-16
AD7510DISE	-55°C to +125°C	E-20A
AD7511DIKN	0 to +70°C	N-16
AD7511DIKP	0 to +70°C	P-20A
AD7511DIKQ	-25°C to +85°C	Q-16
AD7511DISQ	-55°C to +125°C	Q-16
AD7511DITE	-55°C to +125°C	E-20A
AD7512DIKN	0 to +70°C	N-14
AD7512DIKP	0 to +70°C	P-20A
AD7512DIKQ	-25°C to +85°C	Q-14
AD7512DITQ	-55°C to +125°C	Q-14
AD7512DITE	-55°C to +125°C	E-20A

NOTES

¹To order MIL-STD-883, Class B, processed parts, add/883B to part number. See Analog Devices Military Products Databook (1990) for military data sheet.

²E = Leadless Ceramic Chip Carrier (LCCC); N = Plastic DIP; P = Plastic Leaded Chip Carrier (PLCC); Q = Cerdip.

REV. A

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AD7510DI/AD7511DI/AD7512DI — SPECIFICATIONS

($V_{DD} = +15V$, $V_{SS} = -15V$, unless otherwise noted.)

INDUSTRIAL VERSION (K)

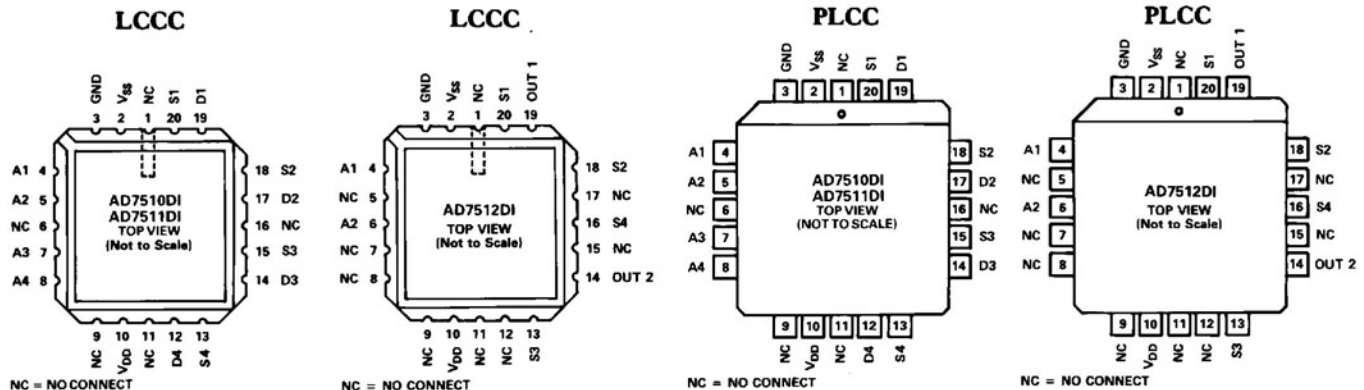
PARAMETER	MODEL	VERSION	+25°C (N, P, Q)	0 to +70°C (N, P) -25°C to +85°C (Q)	TEST CONDITIONS
ANALOG SWITCH					
R_{ON}^1	All	K	75Ω typ, 100Ω max	175Ω max	$-10V \leq V_D \leq +10V$ $I_{DS} = 1.0mA$
R_{ON} vs V_D (V_S)	All	K	20% typ		
R_{ON} Drift	All	K	+0.5%/°C typ		$V_D = 0$, $I_{DS} = 1.0mA$
R_{ON} Match	All	K	1% typ		
R_{ON} Drift Match	All	K	0.01%/°C typ		
I_D (I_S)OFF ¹	All	K	0.5nA typ, 5nA max	500nA max	$V_D = -10V$, $V_S = +10V$ and $V_D = +10V$, $V_S = -10V$
I_D (I_S)ON ¹	All	K	10nA max		$V_S = V_D = +10V$ $V_S = V_D = -10V$
I_{OUT}^1	AD7512DI	K	15nA max	1500nA max	$V_{S1} = V_{OUT} = \pm 10V$, $V_{S2} = \mp 10V$ and $V_{S2} = V_{OUT} = \pm 10V$, $V_{S1} = \mp 10V$
DIGITAL CONTROL					
V_{INL}^1	All	K		0.8V max	
V_{INH}^1	All	K		2.4V min	
C_{IN}	All	K	7pF typ		
I_{INH}^1	All	K	10nA max		$V_{IN} = V_{DD}$
I_{INL}^1	All	K	10nA max		$V_{IN} = 0$
DYNAMIC CHARACTERISTICS					
t_{ON}	AD7510DI	K	180ns typ		$V_{IN} = 0$ to +3.0V
	AD7511DI	K	350ns typ		
t_{OFF}	AD7510DI	K	350ns typ		
	AD7511DI	K	180ns typ		
$t_{TRANSITION}$	AD7512DI	K	300ns typ		
C_S (C_D)OFF	All	K	8pF typ		V_D (V_S) = 0V
C_S (C_D)ON	All	K	17pF typ		
C_{DS} (C_{S-OUT})	All	K	1pF typ		
C_{DD} (C_{SS})	All	K	0.5pF typ		
C_{OUT}	AD7512DI	K	17pF typ		
Q_{INJ}	All	K	30pC typ		
POWER SUPPLY					
I_{DD}^1	All	K	800μA max	800μA max	All digital inputs = V_{INH}
I_{SS}^1	All	K	800μA max	800μA max	
I_{DD}^1	All	K	500μA max	500μA max	All digital inputs = V_{INL}
I_{SS}^1	All	K	500μA max	500μA max	

NOTES

¹ 100% tested.

Specifications subject to change without notice.

PIN CONFIGURATIONS



EXTENDED VERSIONS (S, T)

PARAMETER	MODEL	VERSION	+25°C	-55°C to +125°C	TEST CONDITIONS
ANALOG SWITCH					
R_{ON}^1	All	S, T	100Ω max	175Ω max	$-10V \leq V_D \leq +10V$ $I_{DS} = 1mA$
$I_D (I_S)_{OFF}^1$	All	S, T	3nA max	200nA max	$V_D = -10V, V_S = +10V$ and $V_D = +10V, V_S = -10V$
$I_D (I_S)_{ON}^1$	All	S, T	10		$V_S = V_D = +10V$ and $V_S = V_D = -10V$
I_{OUT}^1	AD7512DI	S, T	9nA max	600nA max	$V_{S1} = V_{OUT} = \pm 10V$ $V_{S2} = \mp 10V$ and $V_{S2} = V_{OUT} = \pm 10V$ $V_{S1} = \mp 10V$
DIGITAL CONTROL					
V_{INL}^1	All	S, T		0.8V max	
$V_{INH}^{1,2}$	AD7510DI	S		2.4V min	
	AD7511DI	T		2.4V min	
	AD7512DI	T		2.4V min	
	AD7511DI	S		3.0V min	
	AD7512DI	S		3.0V min	
I_{INH}^1	All	S, T	10nA max		$V_{IN} = V_{DD}$
I_{INL}^1	All	S, T	10nA max		$V_{IN} = 0$
DYNAMIC CHARACTERISTICS					
t_{ON}^3	AD7510DI	S,	1.0μs max		$V_{IN} = 0$ to +3V
	AD7511DI	S, T	1.0μs max		
t_{OFF}^3	AD7510DI	S, T	1.0μs max		
	AD7511DI	S, T	1.0μs max		
$t_{TRANSITION}^3$	AD7512DI	S, T	1.0μs max		
POWER SUPPLY					
I_{DD}^1	All	S, T		800μA max	All digital inputs = V_{INH}
I_{SS}^1	All	S, T		800μA max	
I_{DD}^1	All	S, T		500μA max	All digital inputs = V_{INL}
I_{SS}^1	All	S, T		500μA max	

NOTES

¹ 100% tested.

² A pullup resistor, typically 1-2kΩ is required to make AD7511DISQ and AD7512DISQ TTL compatible.

³ Guaranteed, not production tested.

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ABSOLUTE MAXIMUM RATINGS*

V_{DD} to GND +17V

V_{SS} to GND -17V

Overvoltage at $V_D (V_S)$

(1 second surge) $V_{DD} + 25V$
or $V_{SS} - 25V$

(Continuous) $V_{DD} + 20V$
or $V_{SS} - 20V$

or 20mA, Whichever Occurs First

Switch Current (I_{DS} , Continuous) 50mA

Switch Current (I_{DS} , Surge)

1ms Duration, 10% Duty Cycle 150mA

Digital Input Voltage Range 0V to $V_{DD} + 0.3V$

Power Dissipation (Any Package)

Up to +75°C 450mW

Derates above +75°C by 6mW/°C

Lead Temperature (Soldering, 10sec) +300°C

Storage Temperature -65°C to +150°C

Operating Temperature

Commercial (KN, KP Versions) 0 to +70°C

Industrial (KQ Versions) -25°C to +85°C

Extended (SQ, TQ, SE, TE Versions) -55°C to +125°C

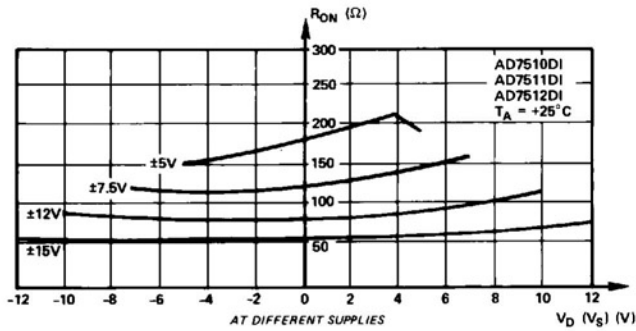
*Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

CAUTION

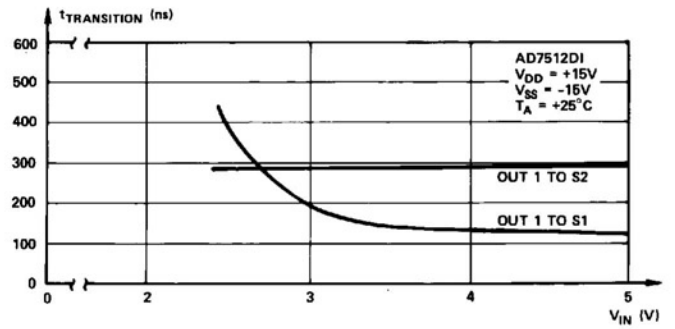
ESD (electrostatic discharge) sensitive device. The digital control inputs are diode protected; however, permanent damage may occur on unconnected devices subject to high energy electrostatic fields. Unused devices must be stored in conductive foam or shunts. The protective foam should be discharged to the destination socket before devices are removed.



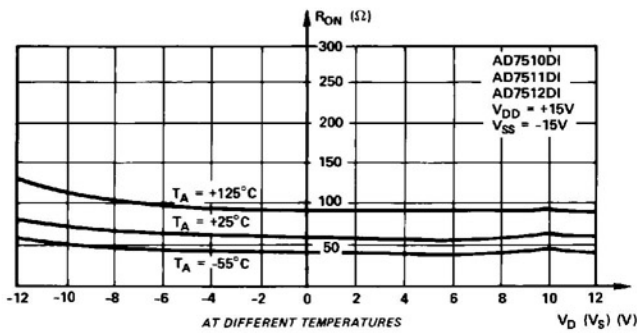
Typical Performance Characteristics—AD7510DI/AD7511DI/AD7512DI



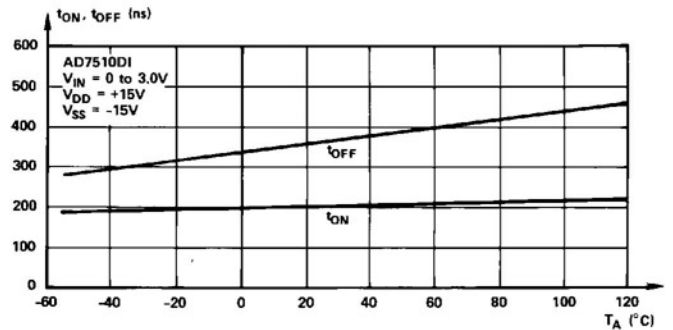
R_{ON} as a Function of V_D (V_S)



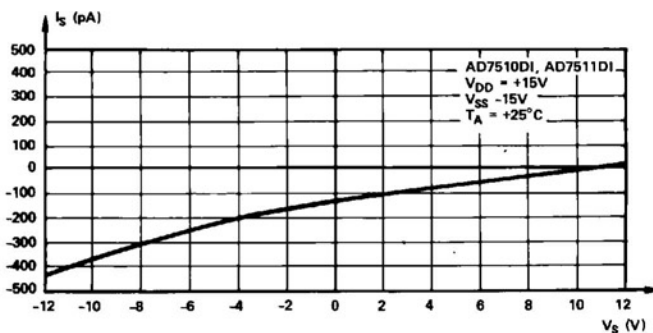
$t_{TRANSITION}$ as a Function of Digital Input Voltage



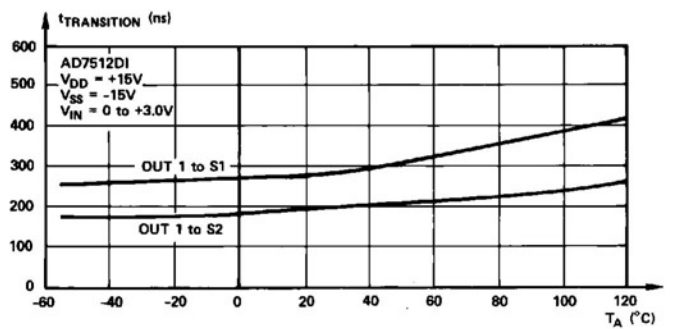
R_{ON} as a Function of V_D (V_S)



t_{ON} , t_{OFF} as a Function of Temperature



I_S , (I_D) $_{OFF}$ vs V_S

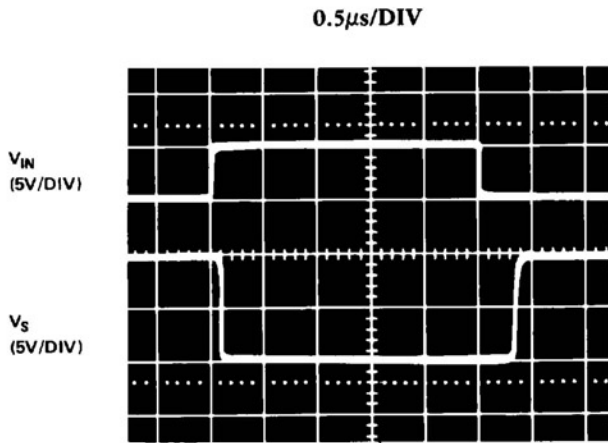


$t_{TRANSITION}$ as a Function of Temperature

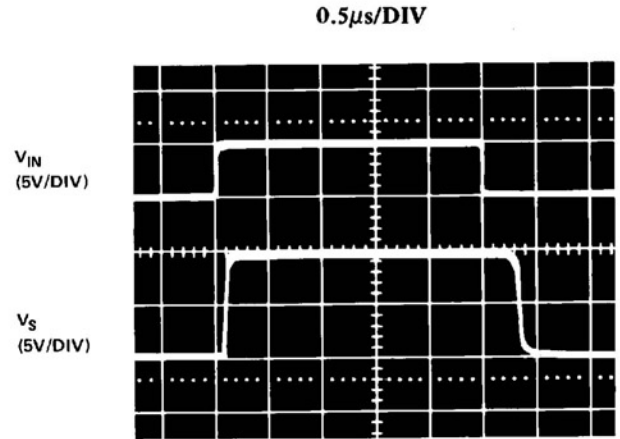
AD7510DI/AD7511DI/AD7512DI

TYPICAL SWITCHING CHARACTERISTICS

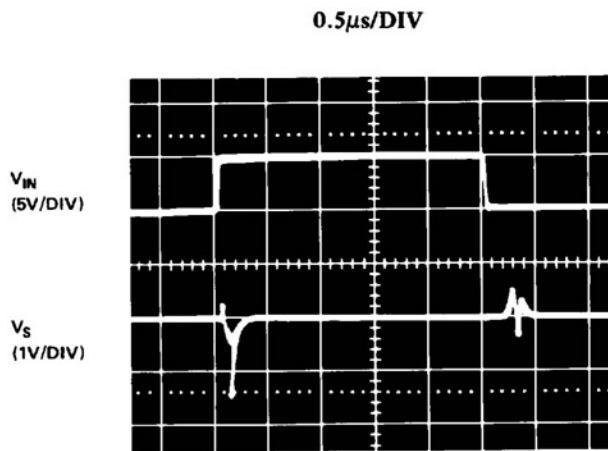
AD7510DI, AD7511DI



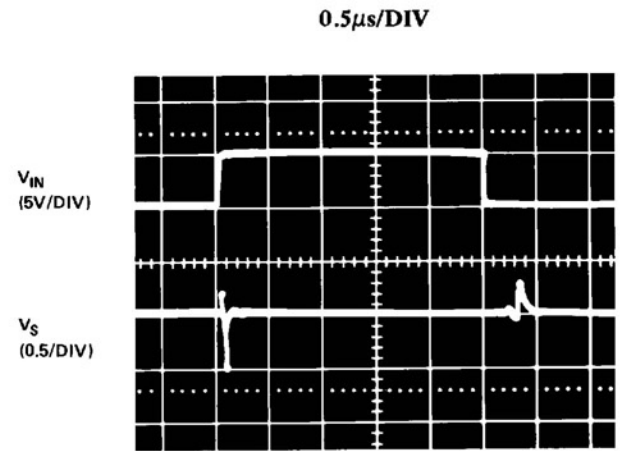
Switching Waveforms for $V_D = -10V$



Switching Waveforms for $V_D = +10V$

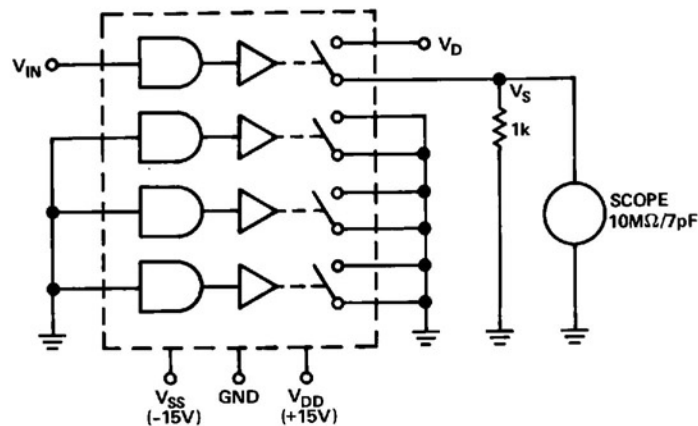


Switching Waveforms for $V_D = \text{Open}$



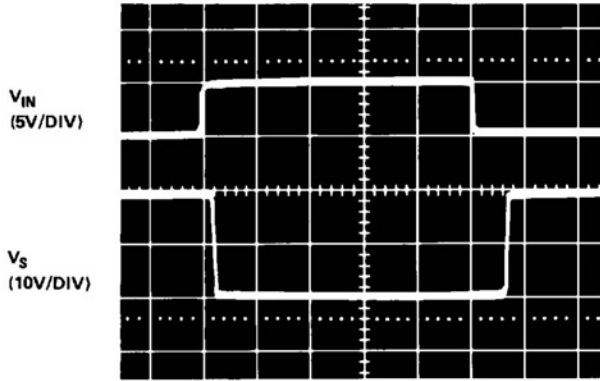
Switching Waveforms for $V_D = 0V$

AD7510DI, AD7511DI TEST CIRCUIT



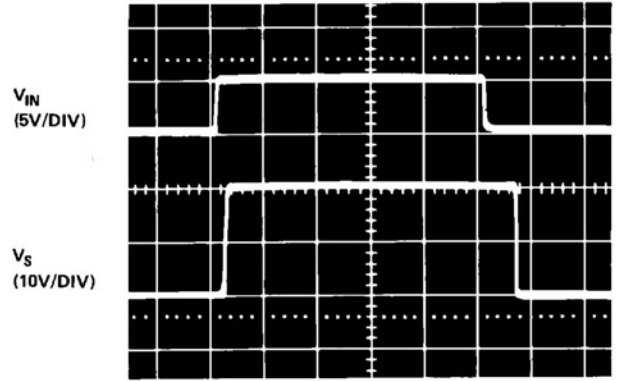
AD7512DI

0.5μs/DIV



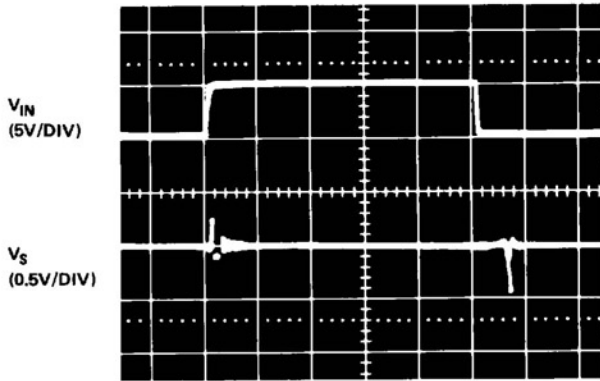
Switching Waveforms for $V_{S1} = -10V$, $V_{S2} = +10V$, $R_L = 1k$

0.5μs/DIV



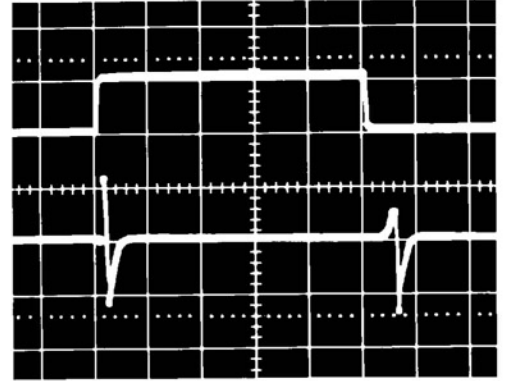
Switching Waveforms for $V_{S1} = +10V$, $V_{S2} = -10V$, $R_L = \infty$

0.5μs/DIV



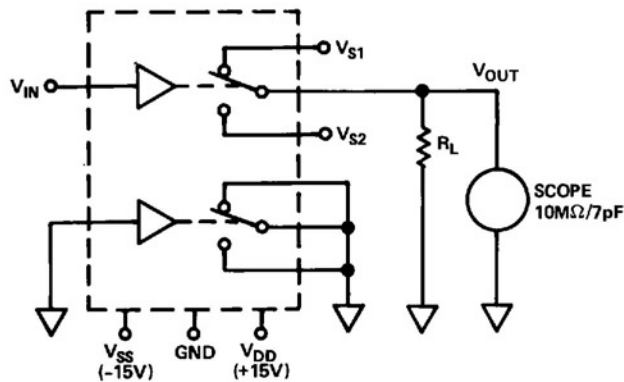
Switching Waveforms for V_{S1} and $V_{S2} = 0V$, $R_L = \infty$

0.5μs/DIV



Switching Waveforms for V_{S1} and $V_{S2} = \text{Open}$, $R_L = 1k$

AD7512DI TEST CIRCUIT



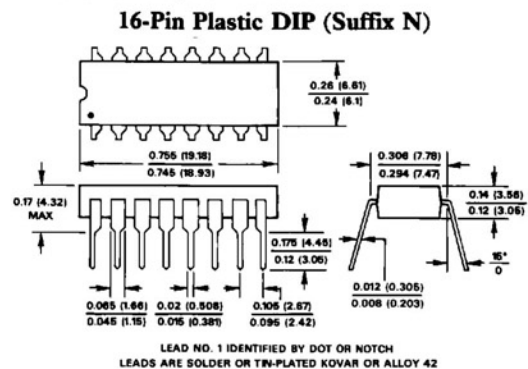
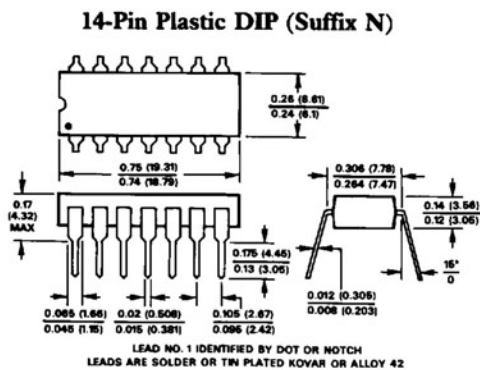
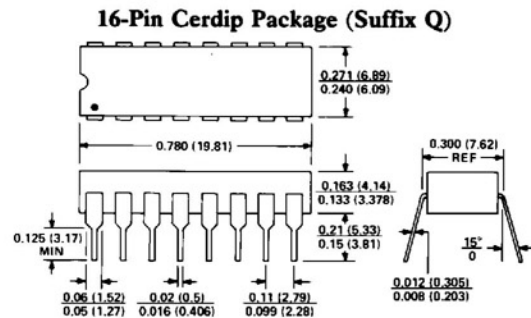
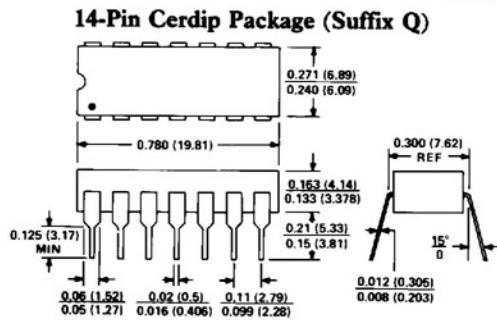
AD7510DI/AD7511DI/AD7512DI

TERMINOLOGY

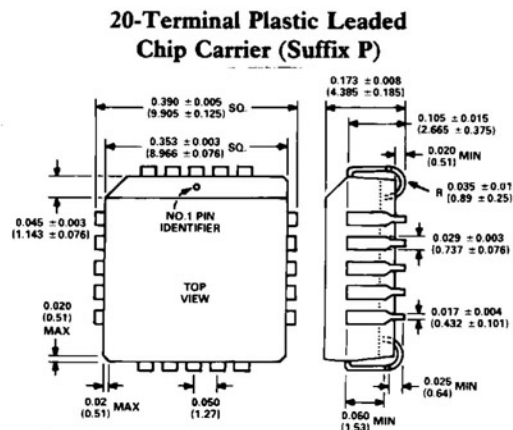
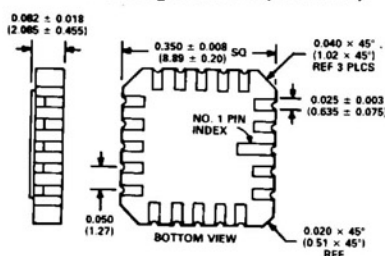
R_{ON}	Ohmic resistance between terminals D and S.	$C_{DD} (C_{SS})$	Capacitance between terminals D (S) of any two switches. (This will determine the cross coupling between switches vs. frequency.)
R_{ON} Drift Match	Difference between the R_{ON} drift of any two switches.	t_{ON}	Delay time between the 50% points of the digital input and switch "ON" condition.
R_{ON} Match	Difference between the R_{ON} of any two switches.	t_{OFF}	Delay time between the 50% points of the digital input and switch "OFF" condition.
$I_D (I_S)_{OFF}$	Current at terminals D or S. This is a leakage current when the switch is "OFF".	$t_{TRANSITION}$	Delay time when switching from one address state to another.
$I_D (I_S)_{ON}$	Leakage current that flows from the closed switch into the body. (This leakage will show up as the difference between the current I_D going into the switch and the outgoing current I_S .)	V_{INL}	Maximum input voltage for a logic low.
$V_D (V_S)$	Analog voltage on terminal D (S).	V_{INH}	Minimum input voltage for a logic high.
$C_S (C_D)$	Capacitance between terminal S (D) and ground. (This capacitance is specified for the switch open and closed.)	$I_{INL} (I_{INH})$	Input current of the digital input.
C_{DS}	Capacitance between terminals D and S. (This will determine the switch isolation over frequency.)	C_{IN}	Input capacitance to ground of the digital input.
		V_{DD}	Most positive voltage supply.
		V_{SS}	Most negative voltage supply.
		I_{DD}	Positive supply current.
		I_{SS}	Negative supply current.

OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).



20-Terminal Leadless Ceramic Chip Carrier (Suffix E)





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